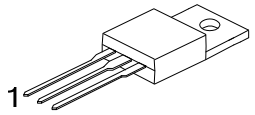
# 75A, 70V N-CHANNEL ENHANCEMENT MODE TRENCH POWER MOSFET



TO-220

## ■ DESCRIPTION

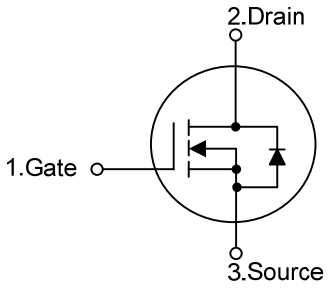
The UTC **UTT75N07** is a N-channel Power MOSFET, it uses UTC's advanced technology to provide the customers with low $R_{DS(ON)}$ and high switching speed characteristic by high cell density trench and low gate charge technology.

The UTC **UTT75N07** is suitable for high efficiency synchronous rectification in SMPS, UPS, hard switched and high frequency circuits.

## ■ FEATURES

* $R_{DS(ON)} \leq 10\ m\Omega$ @ $V_{GS}$=10V, $I_D$=37.5A
* High Cell Density Trench Technology
* High Power and Current Handling Capability

## ■ SYMBOL



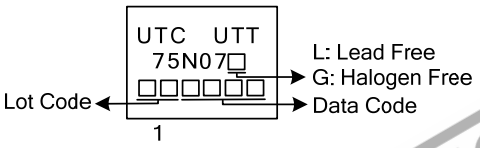

## ■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|---|---|---|---|---|---|---|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| UTT75N07L-TA3-T | UTT75N07G-TA3-T | TO-220 | G | D | S | Tube |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|---|---|
| UTT75N07L-TA3-T<br>(1)Packing Type<br>(2)Package Type<br>(3)Green Package | (1) T: Tube<br>(2) TA3: TO-220<br>(3) L: Lead Free, G: Halogen Free and Lead Free |

## ■ MARKING



## ■ ABSOLUTE MAXIMUM RATING ($T_C$=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 70 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±20 | V |
| Drain Current | Continuous | $I_D$ | 75 | A |
| | Pulsed (Note 2) | $I_{DM}$ | 300 | A |
| Avalanche Energy | Single Pulsed (Note 3) | $E_{AS}$ | 1382 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 13 | V/ns |
| Power Dissipation | | $P_D$ | 110 | W |
| Junction Temperature | | $T_J$ | +150 | °C |
| Storage Temperature Range | | $T_{STG}$ | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 120mH, $I_{AS}$ = 4.8A, $V_{DD}$ = 48V, $R_G$ = 25Ω, Starting $T_J$ = 25°C.
4. $I_{SD}$ ≤30A, di/dt ≤200A/μs, $V_{DD}$ ≤ $V_{(BR)DSS}$, $T_J$ = 25°C.

## ■ THERMAL RESISTANCES CHARACTERISTICS

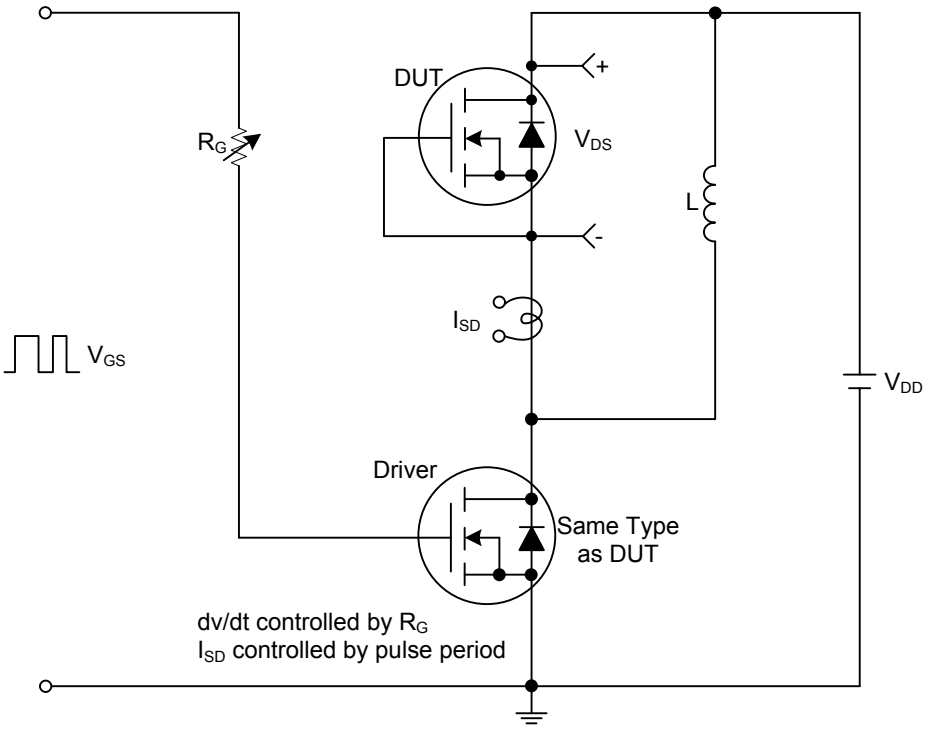
| PARAMETER | SYMBOL | RATINGS | UNIT |
|---|---|---|---|
| Junction to Ambient | $\theta_{JA}$ | 62 | °C/W |
| Junction to Case | $\theta_{JC}$ | 1.13 | °C/W |

## ■ ELECTRICAL CHARACTERISTICS ($T_J$ =25°C, unless otherwise specified)

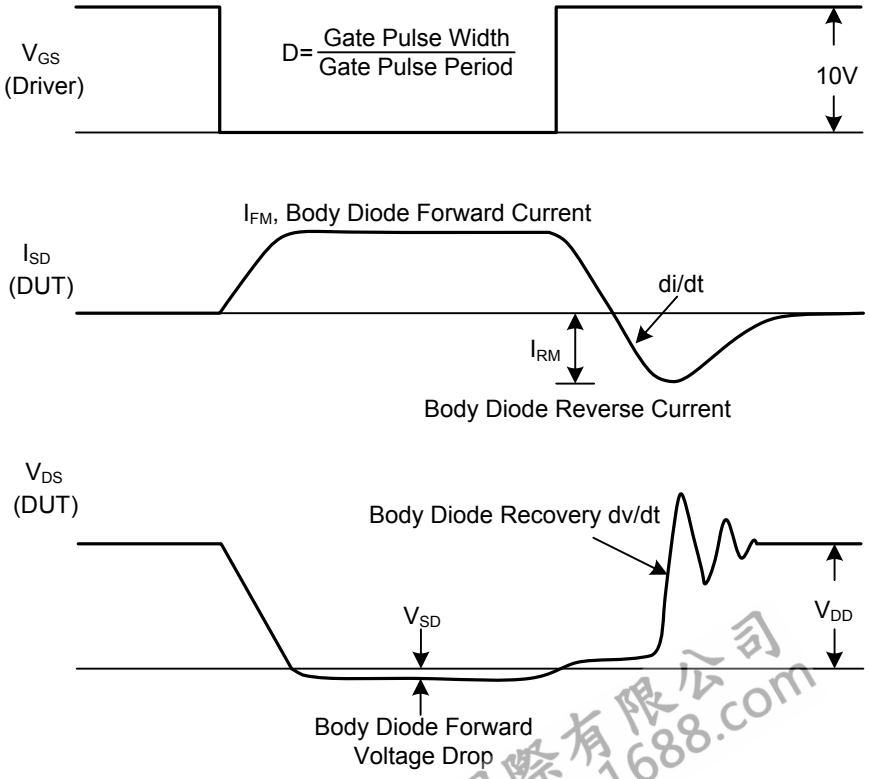
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain-Source Breakdown Voltage | | $BV_{DSS}$ | $I_D$=250μA, $V_{GS}$=0V | 70 | | | V |
| Drain-Source Leakage Current | | $I_{DSS}$ | $V_{DS}$=70V, $V_{GS}$=0V | | | 1.0 | μA |
| Gate-Source Leakage Current | Forward | $I_{GSS}$ | $V_{GS}$=+20V, $V_{DS}$=0V | | | +100 | nA |
| | Reverse | | $V_{GS}$=-20V, $V_{DS}$=0V | | | -100 | nA |
| **ON CHARACTERISTICS** | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}$=$V_{GS}$, $I_D$=250μA | 1.0 | | 3.0 | V |
| Static Drain-Source On-State Resistance | | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=37.5A | | | 10 | mΩ |
| **DYNAMIC PARAMETERS** | | | | | | | |
| Input Capacitance | | $C_{ISS}$ | $V_{GS}$=0V, $V_{DS}$=25V, f=1.0MHz | | 3700 | | pF |
| Output Capacitance | | $C_{OSS}$ | | | 290 | | pF |
| Reverse Transfer Capacitance | | $C_{RSS}$ | | | 245 | | pF |
| **SWITCHING PARAMETERS** | | | | | | | |
| Total Gate Charge (Note 1) | | $Q_G$ | $V_{DS}$=50V, $V_{GS}$=10V, $I_D$=1.3A, $I_G$=100μA (Note 1, 2) | | 430 | | nC |
| Gate to Source Charge | | $Q_{GS}$ | | | 20 | | nC |
| Gate to Drain Charge | | $Q_{GD}$ | | | 34 | | nC |
| Turn-on Delay Time (Note 1) | | $t_{D(ON)}$ | $V_{DD}$=30V, $V_{GS}$=10V, $I_D$=0.5A, $R_G$ =25Ω (Note 1, 2) | | 64 | | ns |
| Rise Time | | $t_R$ | | | 120 | | ns |
| Turn-off Delay Time | | $t_{D(OFF)}$ | | | 1700 | | ns |
| Fall-Time | | $t_F$ | | | 420 | | ns |
| **SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS** | | | | | | | |
| Maximum Body-Diode Continuous Current | | $I_S$ | | | | 75 | A |
| Maximum Body-Diode Pulsed Current | | $I_{SM}$ | | | | 300 | A |
| Drain-Source Diode Forward Voltage (Note 1) | | $V_{SD}$ | $I_S$=75A, $V_{GS}$=0V | | | 1.2 | V |
| Reverse Recovery Time (Note 1) | | $t_{rr}$ | $I_S$=30A, $V_{GS}$=0V, $dI_F/dt$ =100A/μs | | 66 | | nS |
| Reverse Recovery Charge | | $Q_{rr}$ | | | 0.1 | | μC |

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

## ■ TEST CIRCUITS AND WAVEFORMS



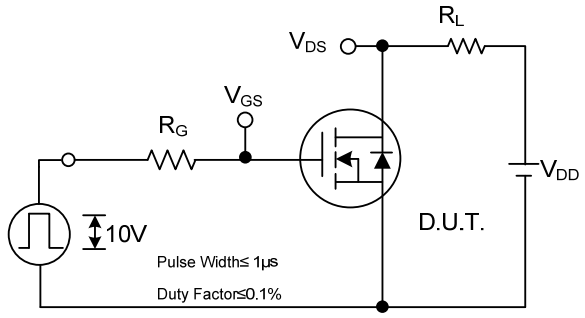

**Peak Diode Recovery dv/dt Test Circuit**



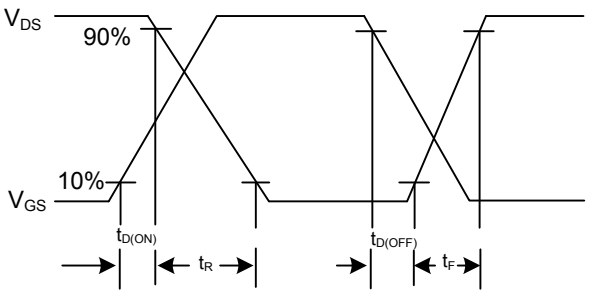

Peak Diode Recovery dv/dt Test Circuit and Waveforms

**Peak Diode Recovery dv/dt Waveforms**

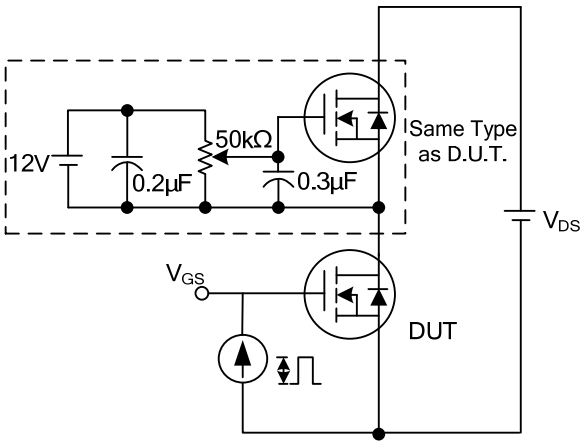
## ■ TEST CIRCUITS AND WAVEFORMS



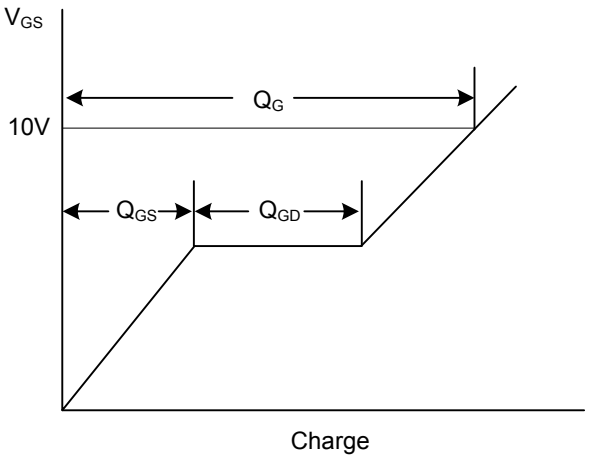

**Switching Test Circuit**



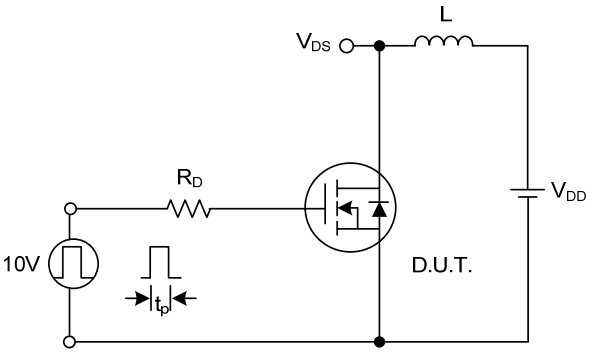

**Switching Waveforms**



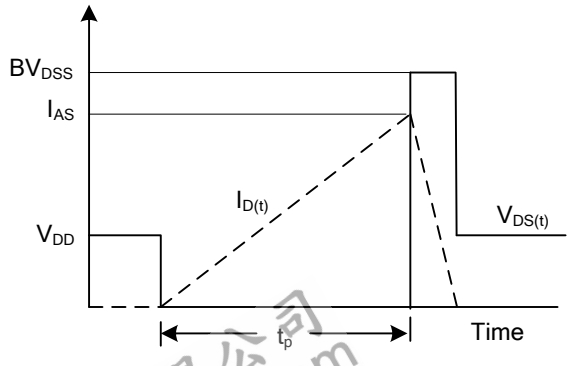

**Gate Charge Test Circuit**




**Gate Charge Waveform**




**Unclamped Inductive Switching Test Circuit**




**Unclamped Inductive Switching Waveforms**